

9

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-060579
 (43)Date of publication of application : 06.03.2001

(51)Int.Cl.

H01L 21/3065
 C23C 16/505
 C23F 4/00
 H01L 21/31
 H05H 1/46

(21)Application number : 11-234103
 (22)Date of filing : 20.08.1999

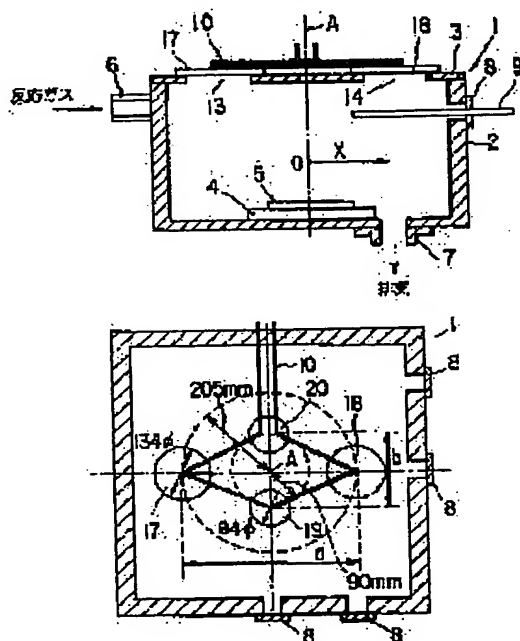
(71)Applicant : TOSHIBA CORP
 (72)Inventor : SANGA MASASHI

(54) PLASMA TREATING METHOD AND PLASMA TREATMENT APPARATUS

(57)Abstract:

PROBLEM TO BE SOLVED: To eliminate the need for increasing the area of a dielectric window, even if region generating plasma increases, and allow the window to be thin.

SOLUTION: Four circular holes 13, 14 are formed into a metal top plate 3 attached to a reactor chamber 1, and circular dielectric windows 17-20 are provided in these holes 13, 14 and located on circles which have different diameters with the center at a center axis A of an induced magnetic field by an antenna 10, i.e., at the points of cutting off eddy currents generated by the induced magnetic field on the metal top plate 3 of the reaction chamber 1.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's